

**isc N-Channel MOSFET Transistor**

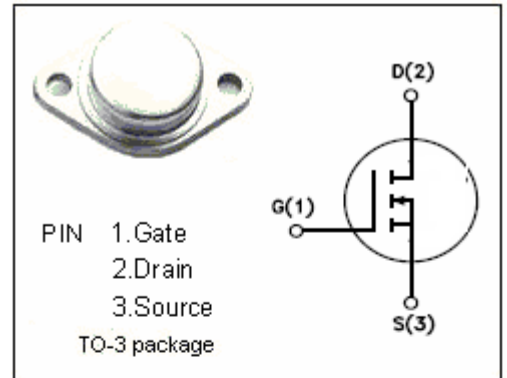
**2N6767**

**DESCRIPTION**

- VGS Rated at  $\pm 20V$
- Silicon Gate for fast switching speeds
- $I_{DSS}$ 、 $R_{DS(ON)}$ 、specified at elevated temperature
- Low drive requirements

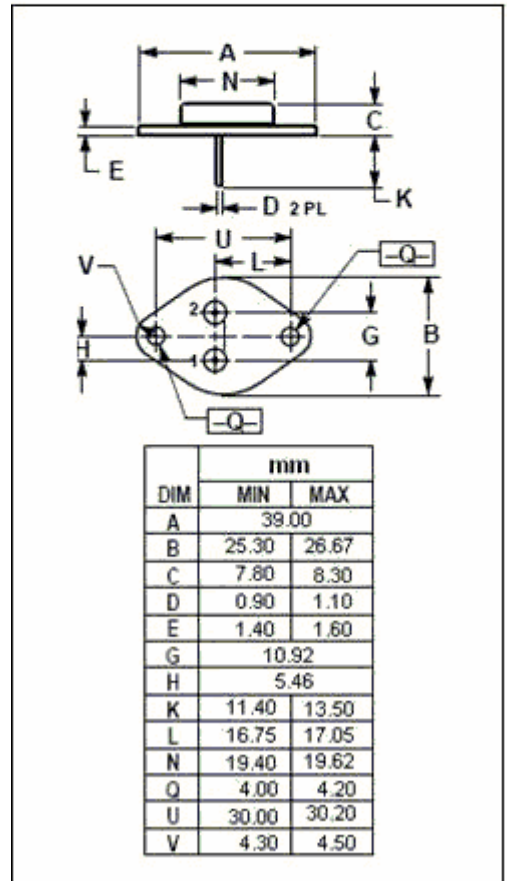
**APPLICATIONS**

designed for high power ,high speed application ,such as switching applies,UPS,AC and DC motor controls , relay and high energy pulse circuits.



**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	ARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	350	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $TC=37^\circ C$	12	A
$P_{tot}$	Total Dissipation@ $TC=25^\circ C$	150	W
$T_j$	Max. Operating Junction Temperature	-55~150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	0.83	$^\circ C/W$

**isc N-Channel Mosfet Transistor****2N6767****• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA	350		V
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 1mA	2	4	V
R <sub>DS(ON)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 7.75A		0.4	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = 20V; V <sub>DS</sub> = 0		100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 350V; V <sub>GS</sub> = 0		1	mA
V <sub>SD</sub>	Diode Forward Voltage	I <sub>F</sub> = 12A; V <sub>GS</sub> = 0		1.6	V